

A cross-sectional view of a semiconductor device 40. The device is built on a substrate 1, which is covered by a layer 2. A series of rectangular blocks 3 are formed on layer 2. Each block 3 is topped with a layer 4, which is further covered by a layer 5. The blocks 3 are separated by gaps, and the layers 4 and 5 are also separated by gaps. The entire structure is labeled 40.

FIG. 2A

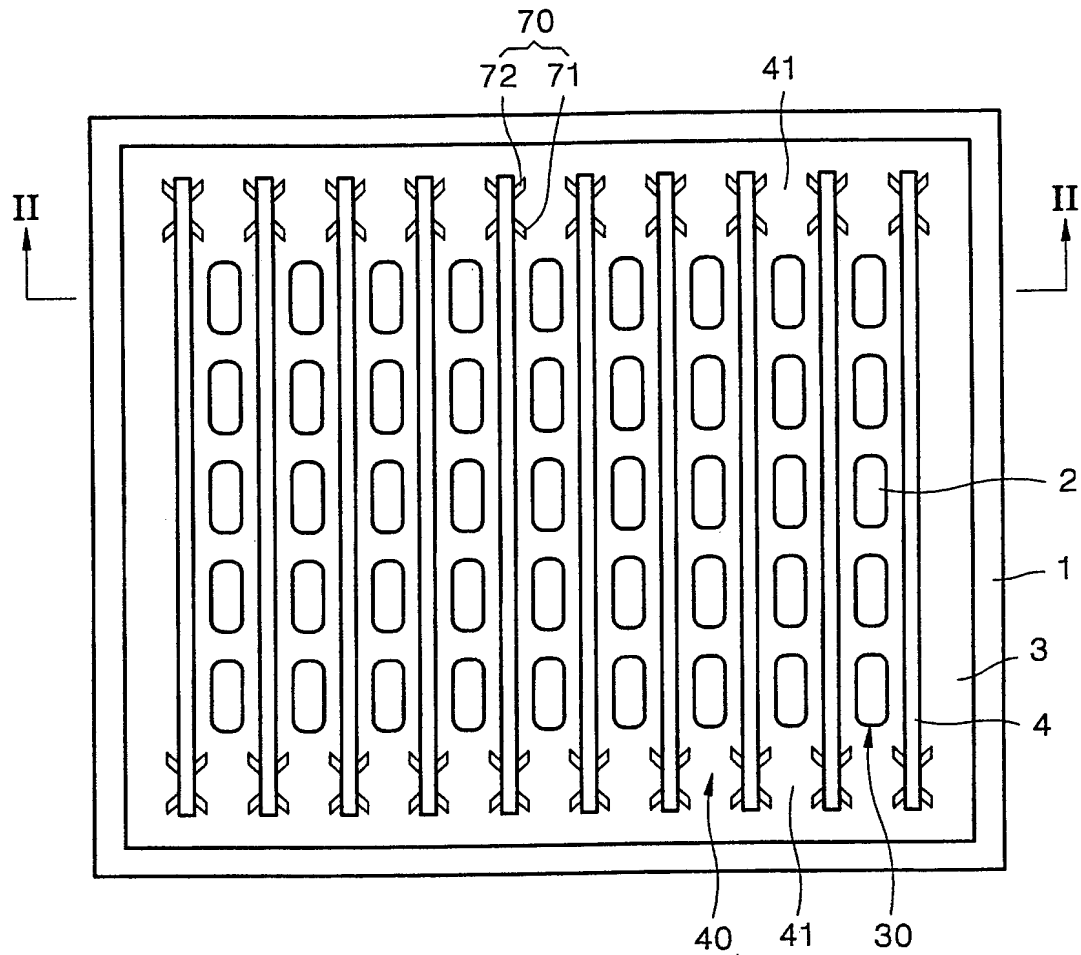


FIG. 2B

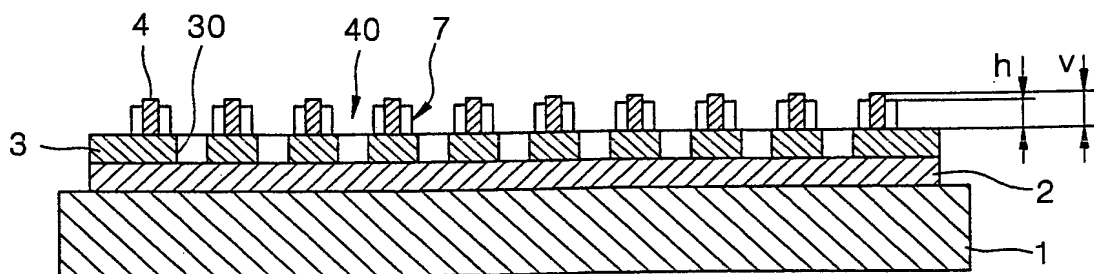




FIG. 4

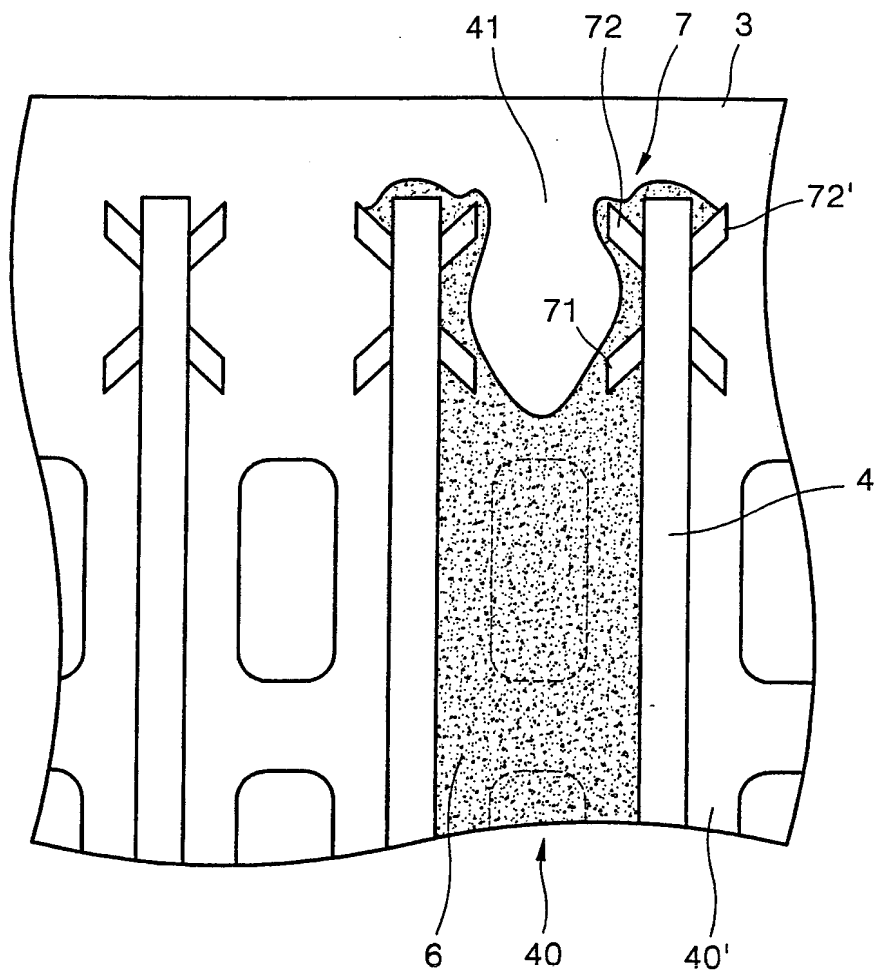


FIG. 5

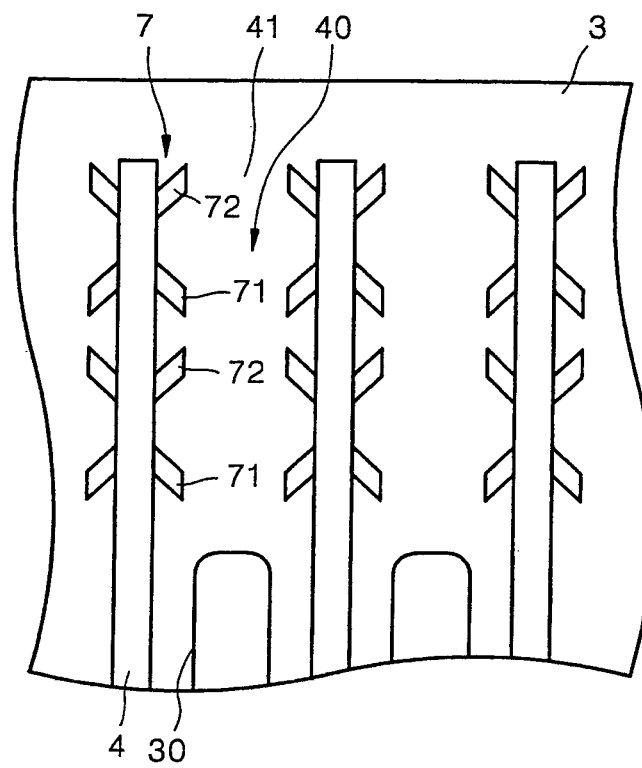
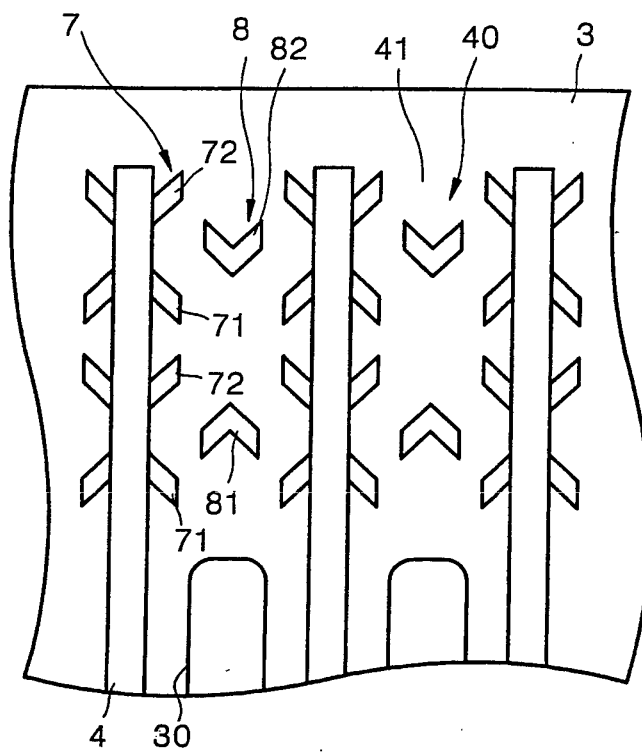


FIG. 6



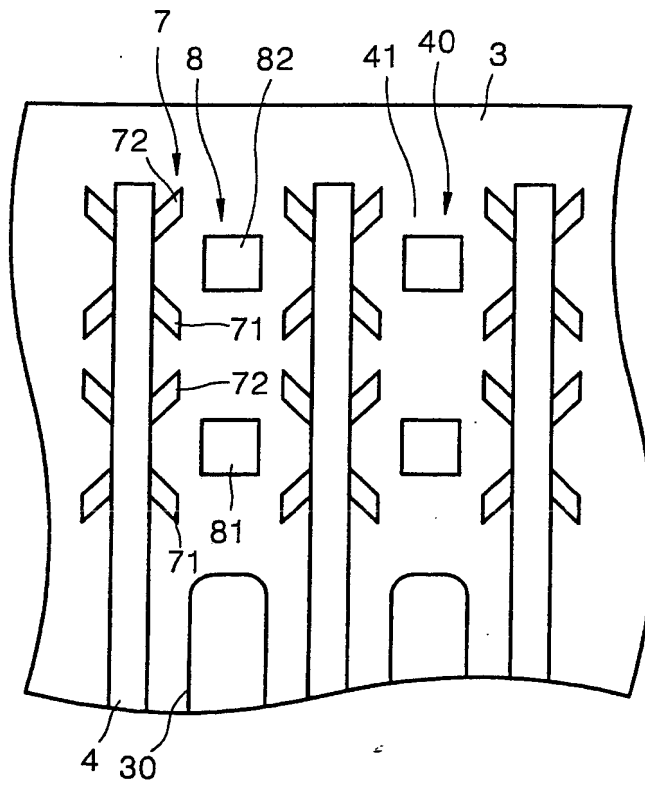
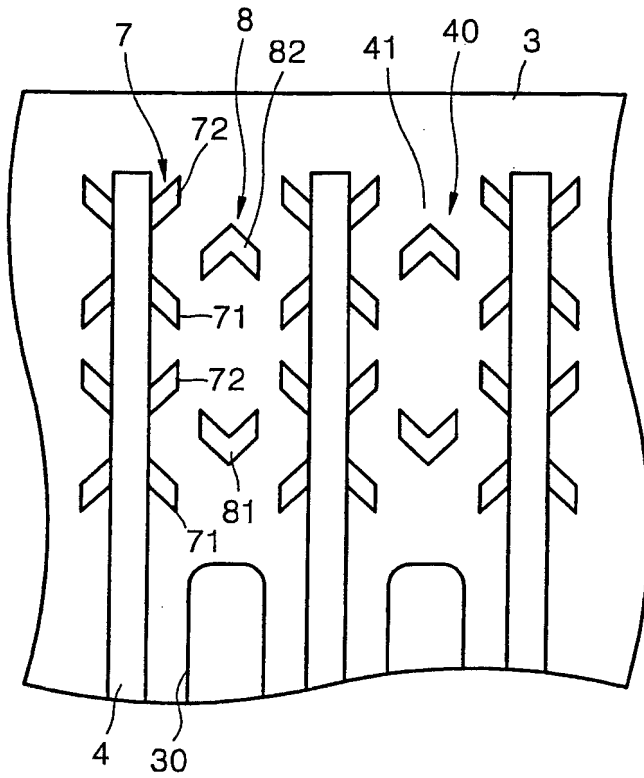


FIG. 9

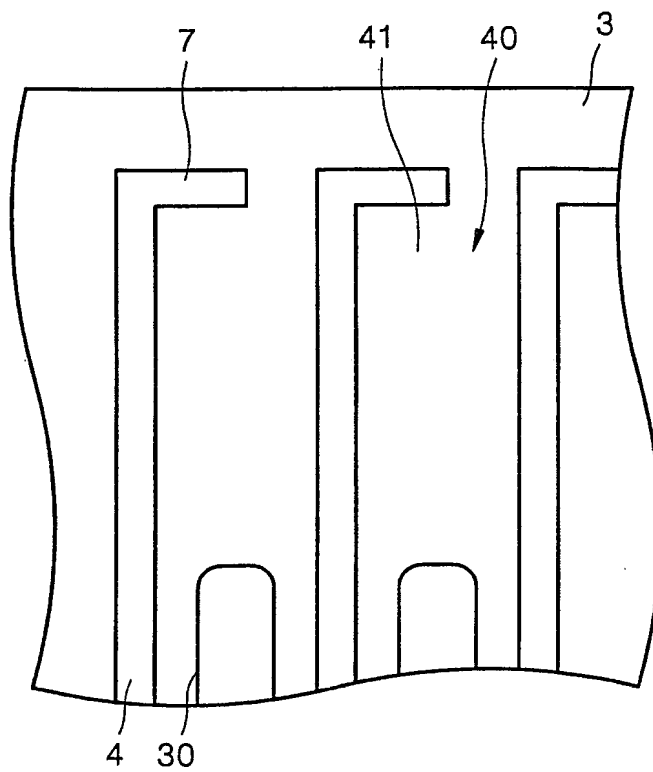


FIG. 10

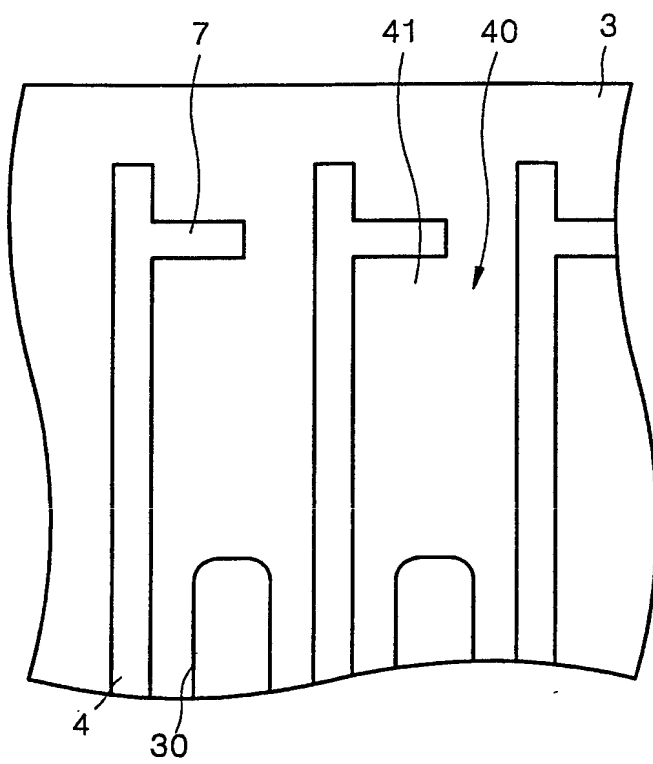


FIG. 11

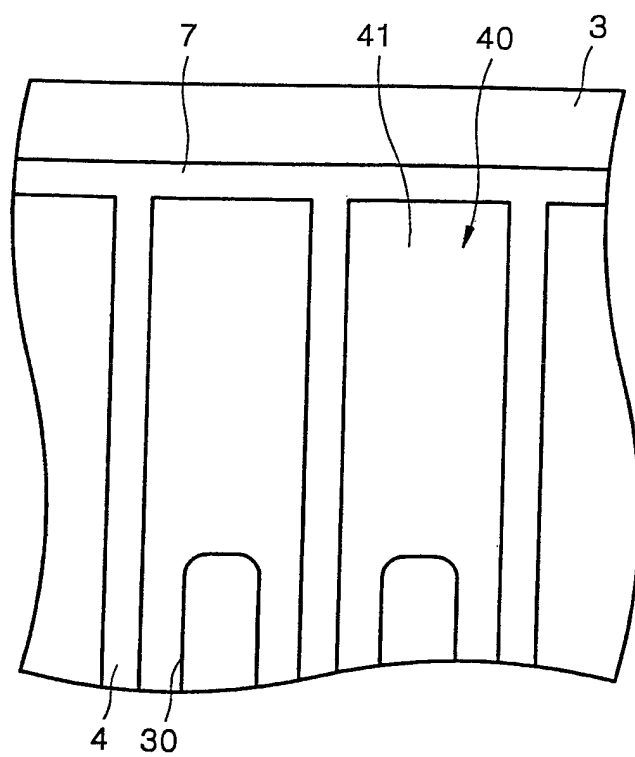




FIG. 12A

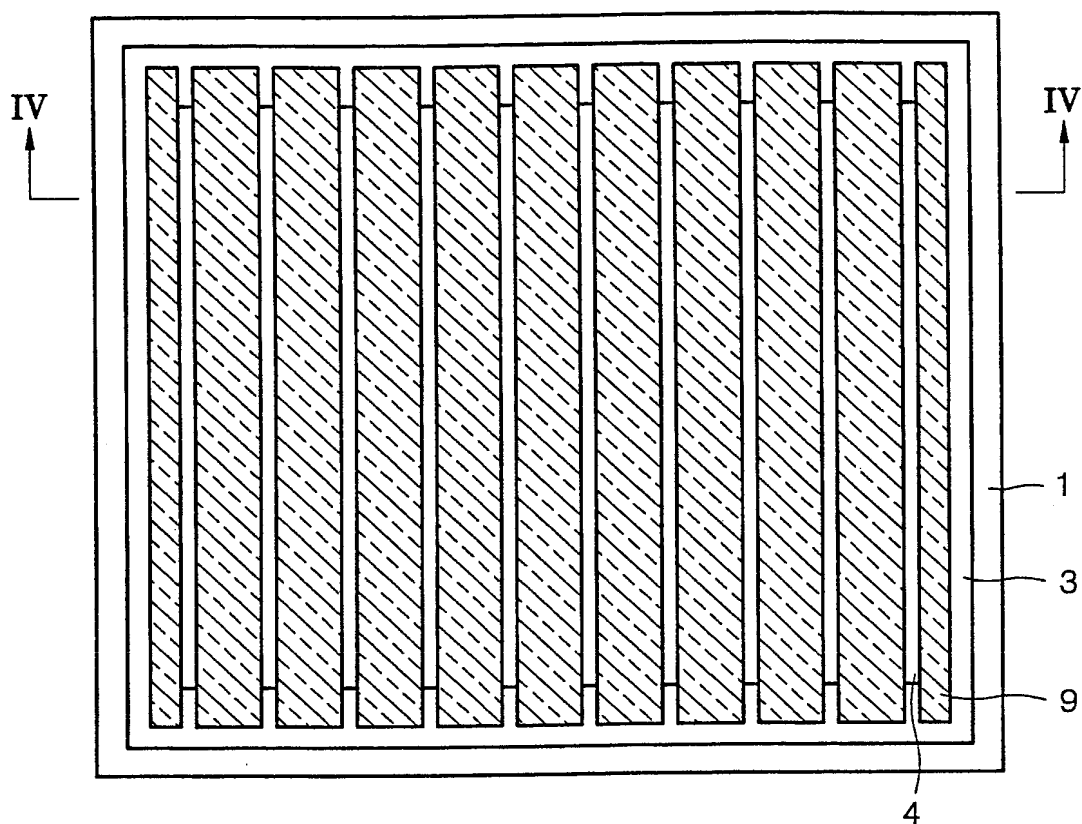


FIG. 12B

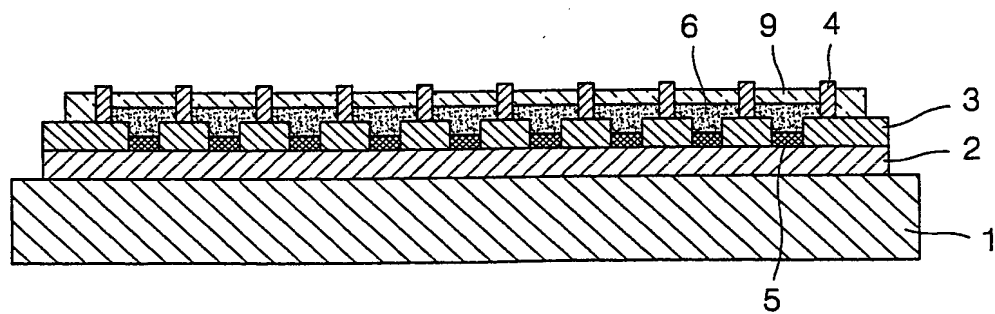


FIG. 13A

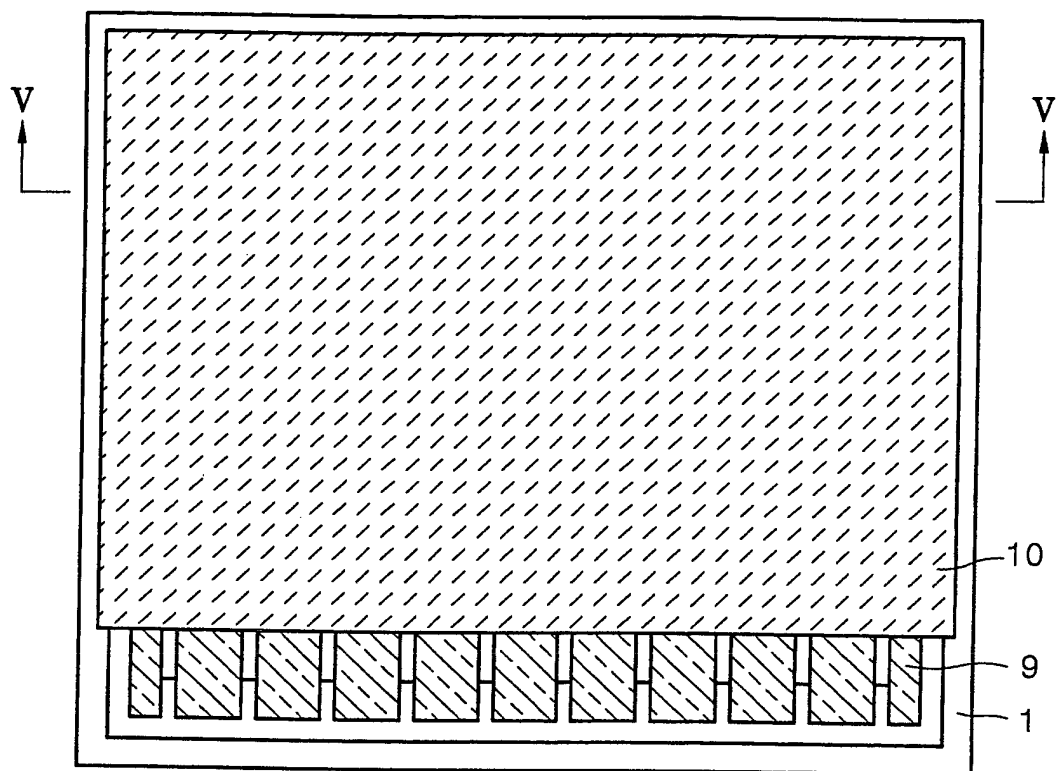


FIG. 13B

